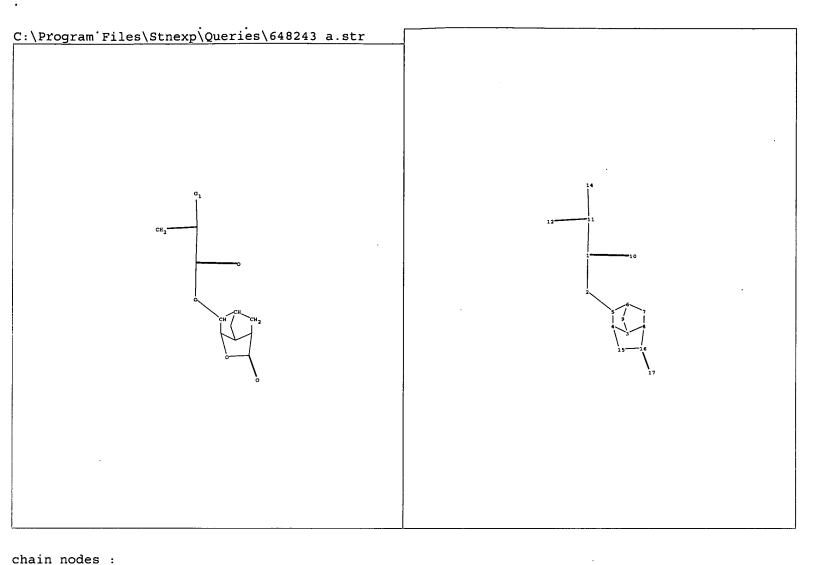
: - : # 648, 243 10/698, PERISTRY FILE N6-=> d his CA/STK sourch, lactore 1-19-06, Ret => d his CA/STK sourch, In Mew claims 13-15,

(FILE 'HOME' ENTERED AT 14:40:46 ON 18 JAN 2006)

	FILE	'REGISTRY' ENTERED AT 14:40:54 ON 18 JAN 2006							
L1		25 S CYCLOPENTYL METHACRYLATE							
L2		16 S CYCLOPENTYL ACRYLATE							
L3		167 S ADAMANTYL METHACRYLATE							
L4		16 S CYCLOPENTYL ACRYLATE 167 S ADAMANTYL METHACRYLATE 54 S ADAMANTYL ACRYLATE							
L5		0 S ADAMANTYLACRYLATE							
L6		1303 S CYCLOHEXYL METHACRYLATE							
L7		378 S CYCLOHEXYL ACRYLATE							
L8		0 S ETHYLADAMANTYL ACRYLATE							
L9		2 S ETHYLADAMANTYL METHACRYLATE							
L10		378 S CYCLOHEXYL ACRYLATE 0 S ETHYLADAMANTYL ACRYLATE 2 S ETHYLADAMANTYL METHACRYLATE 10 S METHYLADAMANTYL METHACRYLATE 1 S (L1 OR L2) AND (L3 OR L4) 6 S (L6 OR L7) AND (L9 OR L10 OR L3 OR L4)							
L11		1 S (I.1 OR I.2) AND (I.3 OR I.4)							
L12		6 S (L6 OR 1.7) AND (1.9 OR 1.10 OR 1.3 OR 1.4)							
L13		2 S L12 AND 2/NC							
נום		2 5 112 AND 2/NC							
	סודם	'CAPLUS' ENTERED AT 14:45:38 ON 18 JAN 2006							
T 1 /									
		12 S L13 2 S 581092-39-9/RN							
ГТ2		2 S 581092-39-9/RN							
		'REGISTRY' ENTERED AT 14:47:44 ON 18 JAN 2006							
L16		1 S (L1 OR L2) AND (L3 OR L4 OR L9 OR L10)							
		'CAPLUS' ENTERED AT 14:49:15 ON 18 JAN 2006							
L17		1 S L16							



```
ring nodes :
    3   4   5   6   7   8   9  15  16

chain bonds :
    1-2  1-10  1-11  2-5  11-12  11-14  16-17

ring bonds :
    3-4  3-8  3-9  4-5  4-15  5-6  6-7  6-9  7-8  8-16  15-16

exact/norm bonds :
    4-15  8-16  11-14  15-16  16-17

exact bonds :
    1-2  1-10  1-11  2-5  3-4  3-8  3-9  4-5  5-6  6-7  6-9  7-8  11-12
```

G1:H,CH3

Match level :

1 2 10 11 12 14 17

1:Atom 2:Atom 3:Atom 4:Atom 5:Atom 6:Atom 7:Atom 8:Atom 9:Atom 10:CLASS 11:Atom 12:Atom 14:Atom 15:Atom 16:Atom 17:Atom

L4 ANSWER 29 OF 29 REGISTRY COPYRIGHT 2006 ACS on STN

RN 254900-09-9 REGISTRY

ED Entered STN: 04 Feb 2000

CN 2-Propenoic acid, 2-methyl-, 2-methyltricyclo[3.3.1.13,7]dec-2-yl ester, polymer with hexahydro-2-oxo-3,5-methano-2H-cyclopenta[b]furan-6-yl 2-propenoate (9CI) (CA INDEX NAME)

OTHER CA INDEX NAMES:

CN 2-Propenoic acid, hexahydro-2-oxo-3,5-methano-2H-cyclopenta[b] furan-6-yl ester, polymer with 2-methyltricyclo[3.3.1.13,7]dec-2-yl 2-methyl-2-propenoate (9CI)

OTHER NAMES:

CN 5-Acryloyloxy-2,6-norbornanecarbolactone-2-methyl-2-adamantyl methacrylate copolymer

MF (C15 H22 O2 . C11 H12 O4) x

CI PMS

PCT Polyacrylic

SR CA

LC STN Files: CA, CAPLUS, USPAT2, USPATFULL

CM 1

CRN 242129-35-7 CMF C11 H12 O4

$$0 \\ C - CH = CH_2$$

CM 2

CRN 177080-67-0 CMF C15 H22 O2

=>

- 3 REFERENCES IN FILE CA (1907 TO DATE)
- 3 REFERENCES IN FILE CAPLUS (1907 TO DATE)

L31 ANSWER 1 OF 1 REGISTRY COPYRIGHT 2006 ACS on STN

RN 854908-07-9 REGISTRY

ED Entered STN: 13 Jul 2005

CN 2-Propenoic acid, 2-methyl-, 1-ethylcyclopentyl ester, polymer with hexahydro-2-oxo-3,5-methano-2H-cyclopenta[b]furan-6-yl 2-propenoate and 3-hydroxytricyclo[3.3.1.13,7]dec-1-yl 2-methyl-2-propenoate (9CI) (CA INDEX NAME)

OTHER NAMES:

CN 5-Acryloyloxy-2,6-norbornanecarbolactone-1-ethylcyclopentyl methacrylate-3-hydroxy-1-adamantyl methacrylate copolymer

MF (C14 H20 O3 . C11 H18 O2 . C11 H12 O4)x

CI PMS

PCT Polyacrylic

SR CA

LC STN Files: CA, CAPLUS

CM 1

CRN 266308-58-1 CMF C11 H18 O2

$$\begin{array}{c|c} \mathsf{O} & \mathsf{CH}_2 \\ \parallel & \parallel \\ \mathsf{O} - \mathsf{C} - \mathsf{C} - \mathsf{Me} \end{array}$$

CM 2

CRN 242129-35-7 CMF C11 H12 O4

CM 3

CRN 115372-36-6 CMF C14 H20 O3

PROPERTY DATA AVAILABLE IN THE 'PROP' FORMAT

- 1 REFERENCES IN FILE CA (1907 TO DATE)
- 1 REFERENCES IN FILE CAPLUS (1907 TO DATE)

```
2005:540707 CAPLUS
AN
DN
     143:86697
     Resist polymer solution and process for producing the same
TI.
     Yamagishi, Takanori; Baba, Hiromitsu
IN
     Maruzen Petrochemical Co., Ltd., Japan
PA
SO
     PCT Int. Appl., 27 pp.
     CODEN: PIXXD2
DT
     Patent
LA
     Japanese
FAN.CNT 1
     PATENT NO.
                         KIND
                                DATE
                                           APPLICATION NO.
     -----
                         ____
                                -----
                                           ______
                                                                   -----
PΤ
     WO 2005057288
                         A1
                                20050623
                                          WO 2004-JP18494
                                                                  20041210
         W: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH,
             CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD,
             GE, GH, GM, HR, HU, ID, IL, IN, IS, KE, KG, KP, KR, KZ, LC, LK,
             LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO,
             NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ,
             TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW
         RW: BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW, AM,
             AZ, BY, KG, KZ, MD, RU, TJ, TM, AT, BE, BG, CH, CY, CZ, DE, DK,
             EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, MC, NL, PL, PT,
             RO, SE, SI, SK, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML,
             MR, NE, SN, TD, TG
                                            JP 2003-413627
     JP 2005173252
                          A2
                                20050630
                                                                   20031211
     JP 3694692
                          B2
                                20050914
PRAI JP 2003-413627
                          Α
                                20031211
     A resist polymer solution comprising a resist polymer containing a repeating
AB
unit
     decomposed by the action of an acid so as to be soluble in alkali and a
     repeating unit having a polar group, the resist polymer dissolved in a
     solvent for coating film formation, wherein the amount of impurities whose
     b.p. is not higher than that of the solvent for coating film formation is
     ≤1 mass% based on the resist polymer. Further, there is provided a
     process for producing a resist polymer solution, comprising the step (1) of
     re-dissolving a solid matter containing a resist polymer in a solvent for
     coating film formation (a) and/or a solvent (b) whose b.p. at atmospheric
     pressure is not higher than that of the solvent (a); and the impurity
     removing step (2) of distilling off the solvent (b) and/or any excess amount of
     solvent (a) in vacuum from the re-dissoln. solution obtained in the step (1).
IT
     854908-07-9P, 5-Acryloyloxy-2,6-norbornanecarbolactone-1-
     ethylcyclopentyl methacrylate-3-hydroxy-1-adamantyl methacrylate copolymer
     RL: IMF (Industrial manufacture); TEM (Technical or engineered material
     use); PREP (Preparation); USES (Uses)
        (resist polymer solution and process for producing the same)
     854908-07-9 CAPLUS
RN
     2-Propenoic acid, 2-methyl-, 1-ethylcyclopentyl ester, polymer with
CN
     hexahydro-2-oxo-3,5-methano-2H-cyclopenta[b]furan-6-yl 2-propenoate and
     3-hydroxytricyclo[3.3.1.13,7]dec-1-yl 2-methyl-2-propenoate (9CI) (CA
     INDEX NAME)
     CM
          1
     CRN
         266308-58-1
     CMF
        C11 H18 O2
```

ANSWER 1 OF 1 CAPLUS COPYRIGHT 2006 ACS on STN

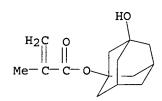
$$\begin{tabular}{c|c} O & CH_2 \\ || & || \\ O-C-C-Me \\ \hline \end{tabular}$$

CM 2

CRN 242129-35-7 CMF C11 H12 O4

CM 3

CRN 115372-36-6 CMF C14 H20 O3



RE.CNT 9 THERE ARE 9 CITED REFERENCES AVAILABLE FOR THIS RECORD ALL CITATIONS AVAILABLE IN THE RE FORMAT

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L15 ANSWER 1 OF 2 CAPLUS COPYRIGHT 2006 ACS on STN
```

AN 2004:816602 CAPLUS

DN 141:322563

TI Polysiloxane substituted with blocked acidic group and photocurable composition for formation of pattern

IN Takahashi, Hideyuki; Ishizeki, Kenji

PA Asahi Glass Co., Ltd., Japan

SO Jpn. Kokai Tokkyo Koho, 19 pp.

CODEN: JKXXAF

DT Patent

LA Japanese

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
ΡI	JP 2004277493	A2	20041007	JP 2003-68215	20030313
PRAI	JP 2003-68215		20030313		

AB The polymer has polysiloxane structure (SiR1R2O)nSiR1R2R3 [I; R1, R2 = H, (cyclo)alkyl, aryl; R3 = H, C1-10 organic group; n = 1-200] and 1-95 weight% of blocked acidic substituents. The polysiloxane may be substituted with fluoroalkyl on ≥2 H. The photocurable composition contains the polysiloxane, another polymer, and a photosensitive acid-generating agent. The another polymer is substituted with blocked acidic groups and is free from structure I and from I whose ≥2 H are replaced by F-substituted C≤20 alkyl. The composition is useful for a precisely patterned mask for preparation of elec. circuits, which shows enhanced ink repellency.

IT **581092-39-9P**, Cyclohexyl methacrylate-2-methyl-2-adamantyl methacrylate copolymer

RL: IMF (Industrial manufacture); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

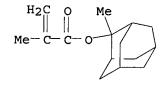
(photocurable composition containing polysiloxane substituted with blocked acidic group and)

RN 581092-39-9 CAPLUS

CN 2-Propenoic acid, 2-methyl-, cyclohexyl ester, polymer with 2-methyltricyclo[3.3.1.13,7]dec-2-yl 2-methyl-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 177080-67-0 CMF C15 H22 O2



CM 2

CRN 101-43-9 CMF C10 H16 O2

L15 ANSWER 2 OF 2 CAPLUS COPYRIGHT 2006 ACS on STN

AN 2003:673878 CAPLUS

DN 139:188322

TI Chemically amplified photoresists for ArF excimer laser lithography and polymers therefor

IN Arita, Yasushi

PA Sumitomo Bakelite Co., Ltd., Japan

SO Jpn. Kokai Tokkyo Koho, 10 pp.

CODEN: JKXXAF

DT Patent

LA Japanese

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
ΡI	JP 2003238629	A2	20030827	JP 2002-41297	20020219
PRAI	JP 2002-41297		20020219		

AB The polymers are a:b:c (molar ratio) cyclohexyl (meth)acrylate-2-methyl-2-adamantyl (meth)acrylate-(meth)acrylic acid derivative copolymers satisfying a/(a + b + c) 0.2-0.8, b/(a + b + c) 0.05-0.5, and c/(a + b + c) 0-0.5, and may satisfy Mn 1000-100,000 and polydispersity >1.0 and ≤2.0. The (meth)acrylic acid derivs. are RC:CH2CO2R' [R' = H, C1-12 (cyclo)alkyl, alkoxyalkyl, cyclic ether, cyclic ester]. Chemical amplified photoresists containing the polymers show excellent sensitivity to ArF excimer laser light and superior high resolution

IT 581092-39-9P, Cyclohexyl methacrylate-2-methyl-2-

adamantylmethacrylate copolymer

RL: IMF (Industrial manufacture); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

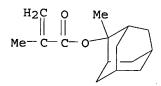
(high-sensitivity and -resolution chemical amplified photoresists for ArF excimer laser lithog.)

RN 581092-39-9 CAPLUS

CN 2-Propenoic acid, 2-methyl-, cyclohexyl ester, polymer with 2-methyltricyclo[3.3.1.13,7]dec-2-yl 2-methyl-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 177080-67-0 CMF C15 H22 O2



CM 2

CRN 101-43-9 CMF C10 H16 O2

=>

bib ab hitstr

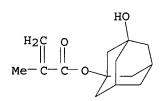
```
ANSWER 1 OF 1 CAPLUS COPYRIGHT 2006 ACS on STN
L17
     2005:540707 CAPLUS
AN
DN
     143:86697
ΤI
     Resist polymer solution and process for producing the same
     Yamagishi, Takanori; Baba, Hiromitsu
IN
PΑ
     Maruzen Petrochemical Co., Ltd., Japan
so
     PCT Int. Appl., 27 pp.
     CODEN: PIXXD2
דת
     Patent
LA
     Japanese
FAN.CNT 1
                       KIND
     PATENT NO.
                                DATE
                                          APPLICATION NO.
                                                                  DATE
     -----
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                                _____
                                           -----
                                                                   _____
                                20050623
PΙ
     WO 2005057288
                         A1
                                         WO 2004-JP18494
                                                                   20041210
         W: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH,
             CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD,
             GE, GH, GM, HR, HU, ID, IL, IN, IS, KE, KG, KP, KR, KZ, LC, LK,
             LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO,
             NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ,
             TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW .
         RW: BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW, AM,
             AZ, BY, KG, KZ, MD, RU, TJ, TM, AT, BE, BG, CH, CY, CZ, DE, DK,
             EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, MC, NL, PL, PT,
             RO, SE, SI, SK, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML,
             MR, NE, SN, TD, TG
     JP 2005173252
                          A2
                                20050630
                                            JP 2003-413627
                                                                   20031211
     JP 3694692
                          B2
                                20050914
PRAI JP 2003-413627
                          Α
                                20031211
     A resist polymer solution comprising a resist polymer containing a repeating
unit
     decomposed by the action of an acid so as to be soluble in alkali and a
     repeating unit having a polar group, the resist polymer dissolved in a
     solvent for coating film formation, wherein the amount of impurities whose
     b.p. is not higher than that of the solvent for coating film formation is
     \leq1 mass% based on the resist polymer. Further, there is provided a
     process for producing a resist polymer solution, comprising the step (1) of
     re-dissolving a solid matter containing a resist polymer in a solvent for
     coating film formation (a) and/or a solvent (b) whose b.p. at atmospheric
     pressure is not higher than that of the solvent (a); and the impurity
     removing step (2) of distilling off the solvent (b) and/or any excess amount of
     solvent (a) in vacuum from the re-dissoln. solution obtained in the step (1).
IT
     854908-07-9P, 5-Acryloyloxy-2,6-norbornanecarbolactone-1-
     ethylcyclopentyl methacrylate-3-hydroxy-1-adamantyl methacrylate copolymer
     RL: IMF (Industrial manufacture); TEM (Technical or engineered material
     use); PREP (Preparation); USES (Uses)
        (resist polymer solution and process for producing the same)
     854908-07-9 CAPLUS
RN
CN
     2-Propenoic acid, 2-methyl-, 1-ethylcyclopentyl ester, polymer with
     hexahydro-2-oxo-3,5-methano-2H-cyclopenta[b]furan-6-yl 2-propenoate and
     3-hydroxytricyclo[3.3.1.13,7]dec-1-yl 2-methyl-2-propenoate (9CI) (CA
     INDEX NAME)
     CM
          1
     CRN
         266308-58-1
     CMF
         C11 H18 O2
```

CM 2

CRN 242129-35-7 CMF C11 H12 O4

CM 3

CRN 115372-36-6 CMF C14 H20 O3



RE.CNT 9 THERE ARE 9 CITED REFERENCES AVAILABLE FOR THIS RECORD ALL CITATIONS AVAILABLE IN THE RE FORMAT

=> d his

(FILE 'HOME' ENTERED AT 14:40:46 ON 18 JAN 2006)

```
FILE 'REGISTRY' ENTERED AT 14:40:54 ON 18 JAN 2006
L1
             25 S CYCLOPENTYL METHACRYLATE
L2
             16 S CYCLOPENTYL ACRYLATE
L3
            167 S ADAMANTYL METHACRYLATE
L4
             54 S ADAMANTYL ACRYLATE
L5
              0 S ADAMANTYLACRYLATE
L6
           1303 S CYCLOHEXYL METHACRYLATE
L7
            378 S CYCLOHEXYL ACRYLATE
L8
              0 S ETHYLADAMANTYL ACRYLATE
L9
              2 S ETHYLADAMANTYL METHACRYLATE
L10
             10 S METHYLADAMANTYL METHACRYLATE
             1 S (L1 OR L2) AND (L3 OR L4)
L11
             6 S (L6 OR L7) AND (L9 OR L10 OR L3 OR L4)
L12
L13
             2 S L12 AND 2/NC
```

